

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE82H140 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

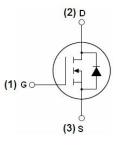
- $V_{DS} = 82V, I_D = 140A$ $R_{DS(ON)} < 5.2m\Omega$ @ $V_{GS} = 10V$ (Typ:4.3mΩ)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Mar	king	Device	Device Package	Reel Size	Tape width	Quantity
NCE82H1	40	NCE82H140	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted) **Parameter Symbol** Unit Limit VDS 82 ٧ **Drain-Source Voltage** Vgs Gate-Source Voltage ±20 **Drain Current-Continuous** 140 I_D Α Drain Current-Continuous(T_C=100 °C) I_D (100°C) 99 Α **Pulsed Drain Current** 480 Α I_{DM} Maximum Power Dissipation P_D 220 W **Derating factor** 1.47 W/°C Single pulse avalanche energy (Note 5) Eas 1500 mJ Operating Junction and Storage Temperature Range T_{J}, T_{STG} -55 To 175 $^{\circ}$ C



Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	Reuc	0.68	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	60	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA 82		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =82V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	4.3	5.2	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	65	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	7900	-	PF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V,	-	445	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	384	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	23	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =1 Ω	-	42	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =2.5 Ω	-	75	-	nS
Turn-Off Fall Time	t _f		-	26	-	nS
Total Gate Charge	Qg	\/ 40\/ L 00A	-	158	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=40V, I_{D}=20A,$	-	32	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	51	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =140A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	140	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	50	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	110	-	nC

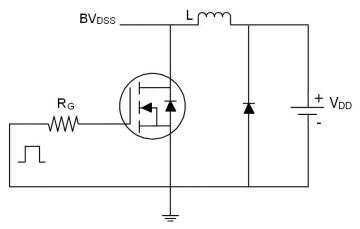
Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^{\circ}$ C,VDD=40V,VG=10V,L=0.5mH,Rg=25 Ω

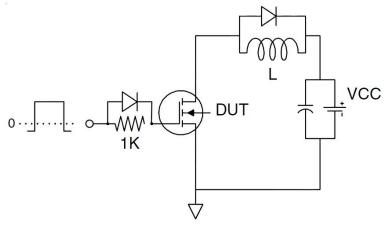


Test circuit

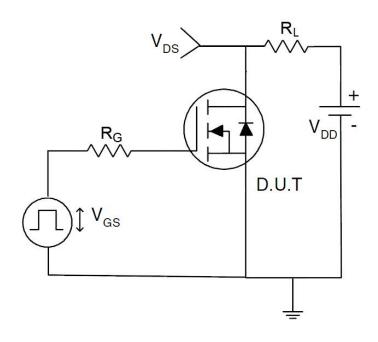
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

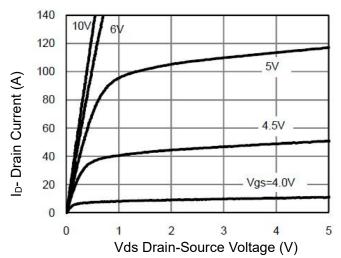


Figure 1 Output Characteristics

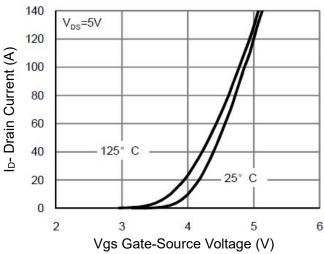


Figure 2 Transfer Characteristics

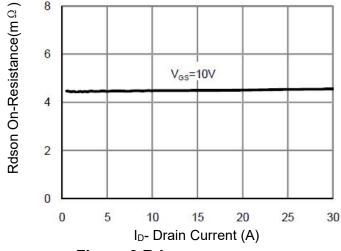


Figure 3 Rdson- Drain Current

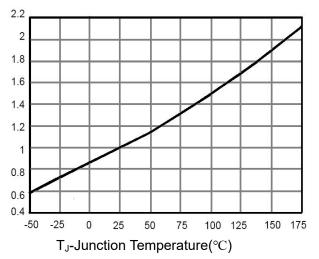


Figure 4 Rdson-JunctionTemperature

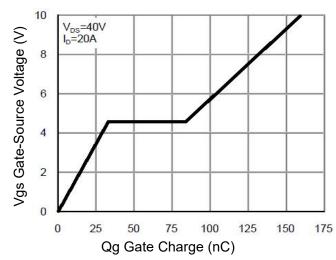


Figure 5 Gate Charge

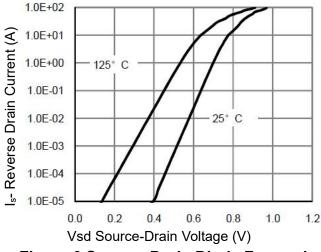


Figure 6 Source- Drain Diode Forward



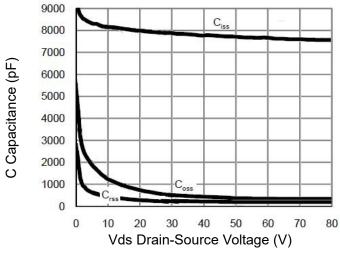


Figure 7 Capacitance vs Vds

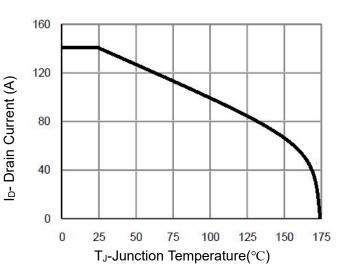


Figure 9 Current De-rating

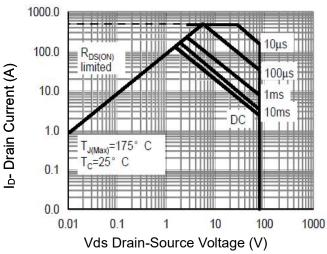


Figure 8 Safe Operation Area

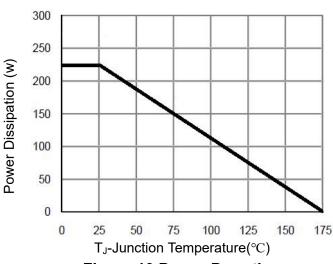


Figure 10 Power De-rating

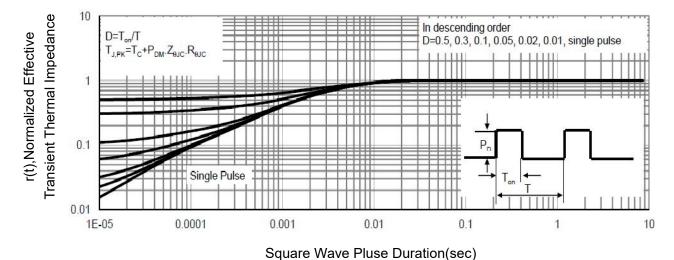
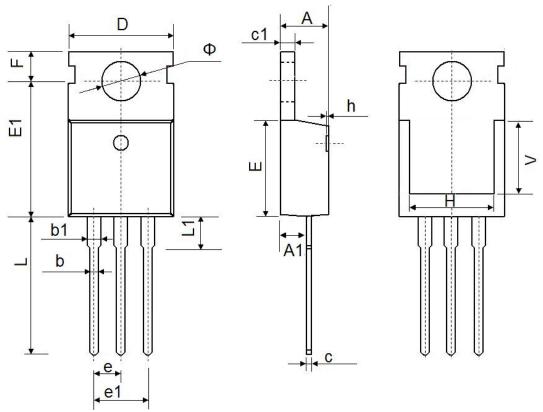


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Comphal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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